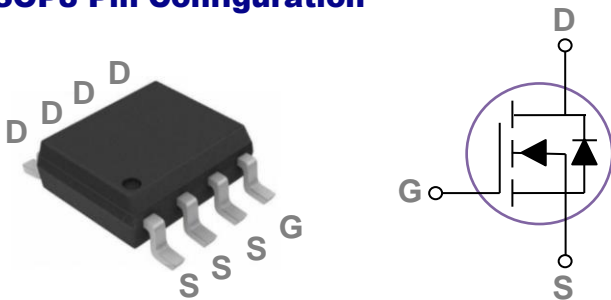


### General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

### SOP8 Pin Configuration



BVDSS	RDSON	ID
100V	19.5mΩ	6A

### Features

- 100V,6A,  $R_{DS(ON)} = 19.5m\Omega$  @  $V_{GS} = 10V$
- Improved  $dv/dt$  capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

### Applications

- Motor Drive
- Power Tools
- LED Lighting
- Quick Charger

### Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_A=25^\circ C$ )	6	A
	Drain Current – Continuous ( $T_A=70^\circ C$ )	4.8	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	24	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	51	mJ
IAS	Single Pulse Avalanched Current <sup>2</sup>	32	A
$P_D$	Power Dissipation ( $T_A=25^\circ C$ )	2	W
	Power Dissipation – Derate above $25^\circ C$	0.016	W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62.5	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100	---	---	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	10	μA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>3</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =2.5A	---	16	19.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	---	21	27	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	1.2	1.6	2.5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =1A	---	6	---	S

**Dynamic and switching Characteristics**

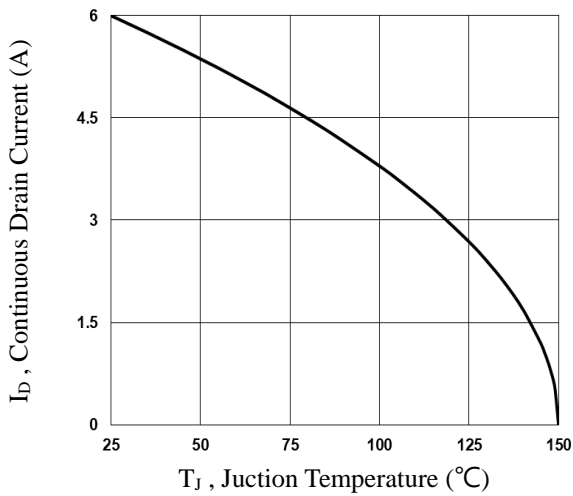
Q <sub>g</sub>	Total Gate Charge <sup>3, 4</sup>	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A	---	12.5	20	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3, 4</sup>		---	1.5	3	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3, 4</sup>		---	4.3	6	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3, 4</sup>	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =3A	---	20	30	ns
T <sub>r</sub>	Rise Time <sup>3, 4</sup>		---	30	45	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3, 4</sup>		---	55	70	
T <sub>f</sub>	Fall Time <sup>3, 4</sup>		---	30	45	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, F=1MHz	---	690	1030	pF
C <sub>oss</sub>	Output Capacitance		---	135	200	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	6	9	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	0.8	---	Ω

**Drain-Source Diode Characteristics and Maximum Ratings**

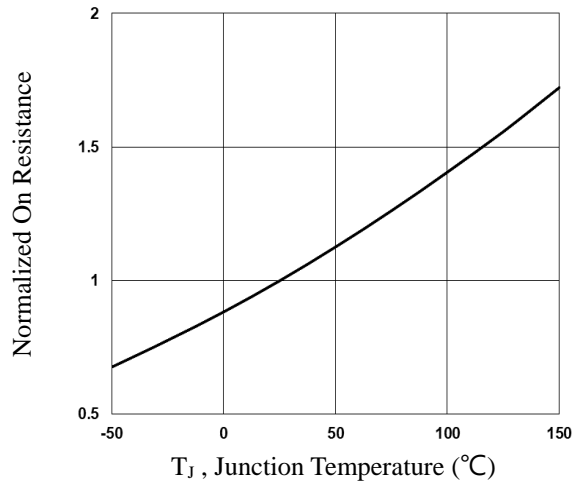
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	6	A
I <sub>SM</sub>	Pulsed Source Current <sup>3</sup>		---	---	12	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>R</sub> =100V, I <sub>S</sub> =3A	---	180	---	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs, T <sub>J</sub> =25°C	---	300	---	nC

Note :

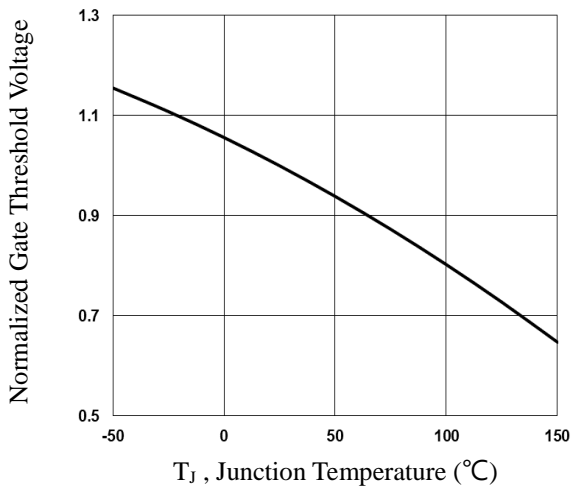
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=50V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=32A., R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



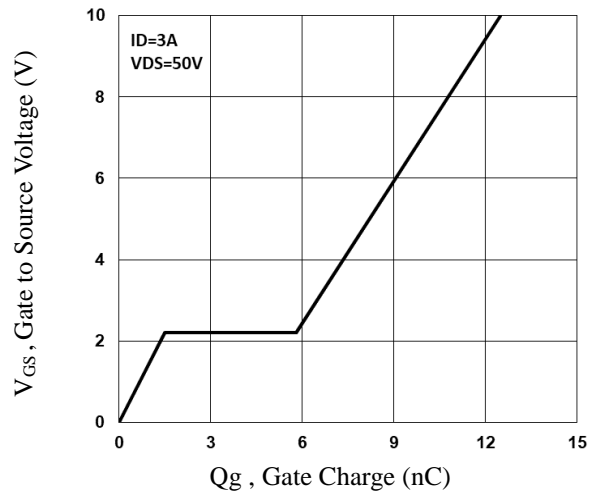
**Fig.1 Continuous Drain Current vs. T<sub>J</sub>**



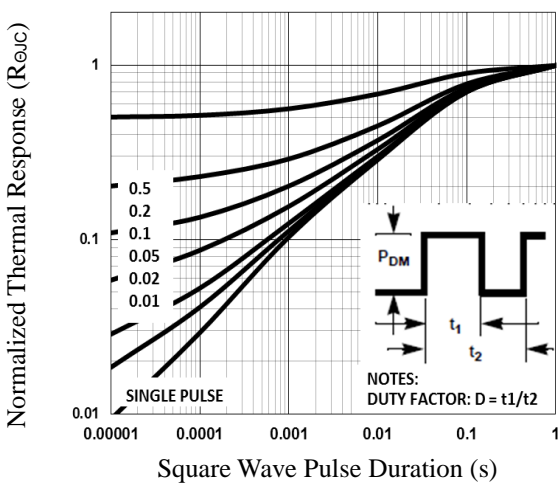
**Fig.2 Normalized R<sub>DS(on)</sub> vs. T<sub>J</sub>**



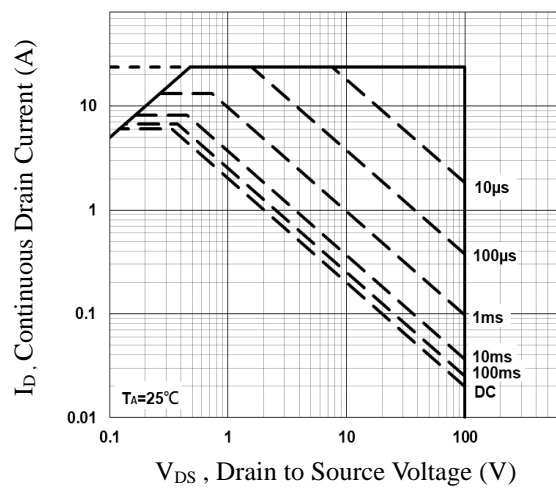
**Fig.3 Normalized V<sub>th</sub> vs. T<sub>J</sub>**



**Fig.4 Gate Charge Waveform**



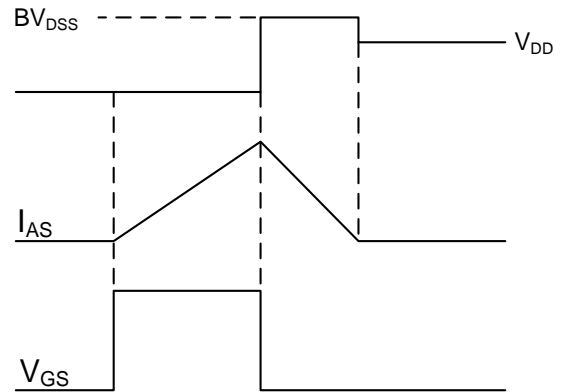
**Fig.5 Normalized Transient Response**



**Fig.6 Maximum Safe Operation Area**

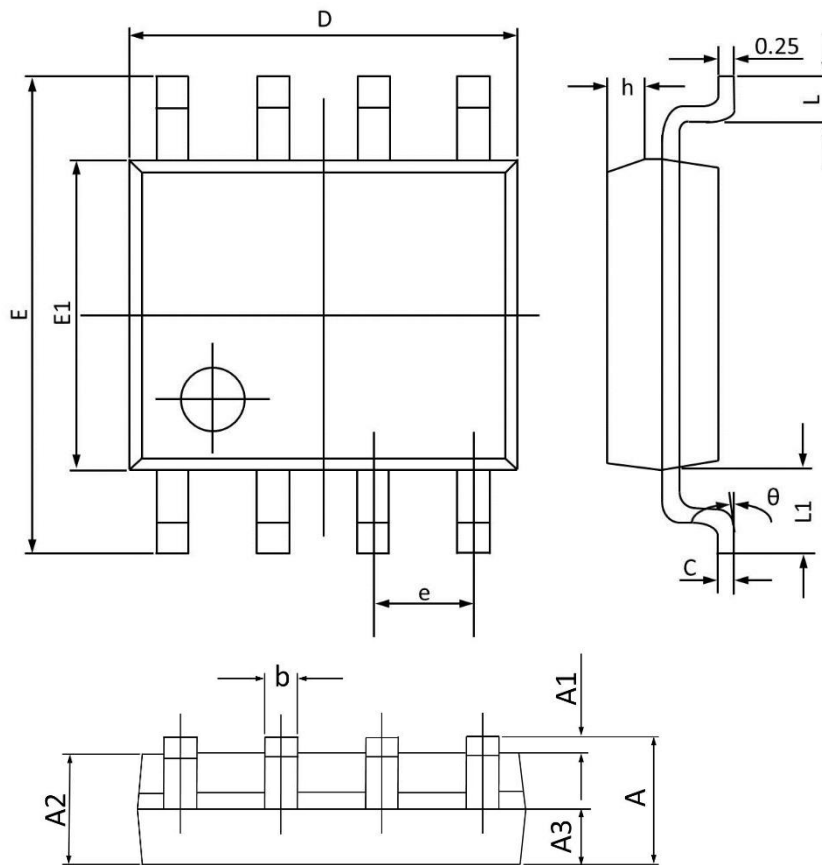


**Fig.7 Switching Time Waveform**



**Fig.8 EAS Waveform**

## SOP8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.800	0.053	0.069
A1	0.050	0.250	0.002	0.010
A2	1.250	1.650	0.049	0.065
A3	0.500	0.700	0.020	0.028
b	0.300	0.510	0.012	0.020
c	0.150	0.260	0.006	0.010
D	4.700	5.100	0.185	0.201
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
e	1.270(BSC)		0.050(BSC)	
h	0.250	0.500	0.010	0.020
L	0.400	1.000	0.016	0.039
L1	1.050(BSC)		0.041(BSC)	
$\theta$	0°	8°	0°	8°